

IN THE CLAIMS

Please amend the claims as follows:

1. (original) Method of manufacturing a magneto-optical device, comprising the steps of embedding at least one coil (3) in an oxide layer (2), providing the oxide layer (2) with at least one aperture (4), selectively etching said aperture (4) in said oxide layer (2) with the use of a sloping side wall (6) of at least one turn (5) of said coil (3).

2. (original) Method according to claim 1, wherein the slope of an inner side wall (6) of an inner turn (5i) of said coil (3) is used for selectively etching said aperture (4), such that said aperture (4) extends above and/or through a center of said coil (3).

3. (currently amended) Method according to claim 1-~~or~~ 2, wherein a first part (2a) of said oxide layer (2) at least extends between said sloping side wall (6) of said coil turn (5) and a surface (7) of the oxide layer (2), viewed in an axial coil direction (Z), and wherein said aperture (4) is formed by etching of at least a portion of a second part (2b) of said oxide layer (2), which second oxide layer part (2a) adjoins said first oxide layer part (2a).

4. (original) Method according to of claim 3, wherein a resist layer (8) is provided on said oxide layer surface (7), wherein said resist layer (8) is provided with an aperture (9) which at least provides access to part of the surface of said second oxide layer part (2b), and wherein said second oxide layer part (2b) is etched by means of an etchant that is provided to said resist aperture (9).

5. (currently amended) Method according to ~~claims 2 and 4~~claim 2, wherein a diameter ( $D_r$ ) of the resist aperture (9) is chosen to be larger than the smallest diameter ( $D_0$ ) of the inner side wall of said inner coil turn (5i), and wherein the diameter ( $D_r$ ) of the resist aperture (9) is chosen smaller than the largest diameter ( $D_1$ ) of the inner side wall of said inner coil winding (5i).

6. (currently amended) Method according to ~~any one of the preceding claims~~claim 1, wherein an etch stop (10) is provided in and/or below said oxide layer (2), such that the etching of said aperture (4) substantially ends when the aperture (4) has reached a desired depth.

7. (currently amended) Method according to ~~any one of the~~  
~~preceding claims~~claim 1, wherein said at least one coil (3) is  
embedded in said oxide layer (2) by at least the following steps:

- depositing a resist layer (21) on a substrate (1);
- patterning the resist layer (21) with a negative coil pattern;
- depositing metal (3), preferably in an electroplating process,  
for forming a metal coil pattern comprising said sloping side wall  
(6);
- removing said patterned resist layer (21); and
- depositing the oxide layer (2), whereupon the surface (7) of the  
oxide layer (2) is preferably planarized.

8. (original) Method according to claim 7, wherein at least one  
metal layer (20) is deposited on the substrate (1) before said  
resist layer (20) is deposited on the substrate (1), and wherein  
said metal (3) and metal layer (20) are partly removed from the  
substrate (1) after the resist (21) has been removed, for example  
by sputter etching.

9. (currently amended) Method according to ~~any one of the~~  
~~preceding claims~~claim 1, wherein said oxide layer (2) at least  
comprises aluminum oxide.

10. (currently amended) Method according to ~~any one of the~~  
~~preceeding claims~~claim 1, wherein a wet etching technique is used  
for etching the aperture (4) in said oxide layer (2).

11. (currently amended) Magneto-optical device, at least  
partially manufactured by the method according to ~~any of the~~  
~~preceeding claims~~claim 1.

12. (original) Use of the magneto-optical device according to  
claim 11 for reading and/or writing information.